

GENERAL PURPOSE APPLICATION.

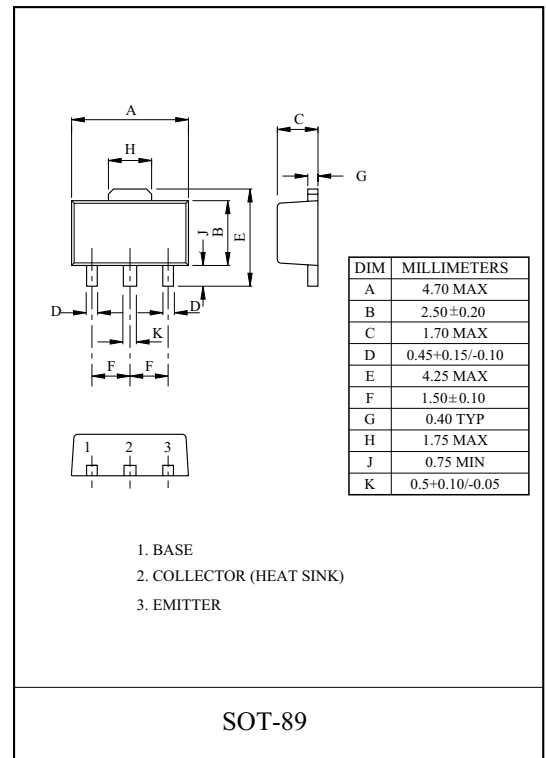
### FEATURES

- 1W (Mounted on Ceramic Substrate).
- Small Flat Package.
- Complementary to KTD1898.

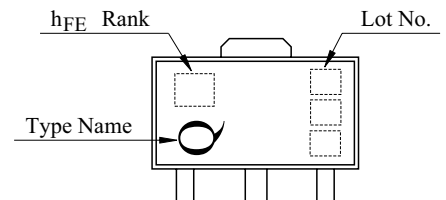
### MAXIMUM RATING (Ta=25 °C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	-80	V
Collector-Emitter Voltage	$V_{CEO}$	-80	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-1	A
Emitter Current	$I_E$	1	A
Collector Power Dissipation	$P_C$	500	mW
	$P_C^*$	1	W
Junction Temperature	$T_j$	150	°C
Storage Temperature Range	$T_{stg}$	-55 ~ 150	°C

\* Mounted on ceramic substrate(250mm<sup>2</sup> × 0.8t)



### Marking

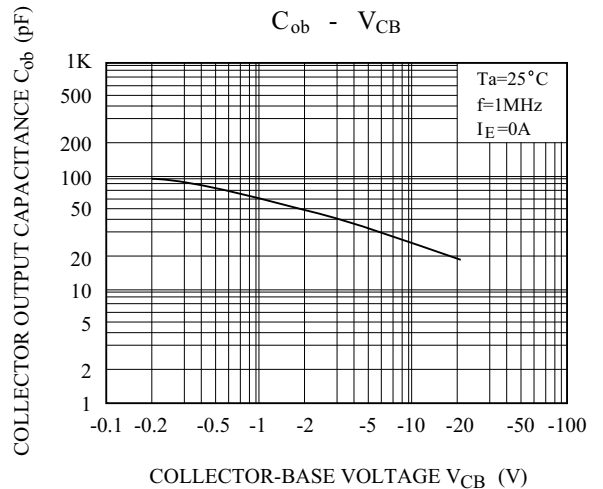
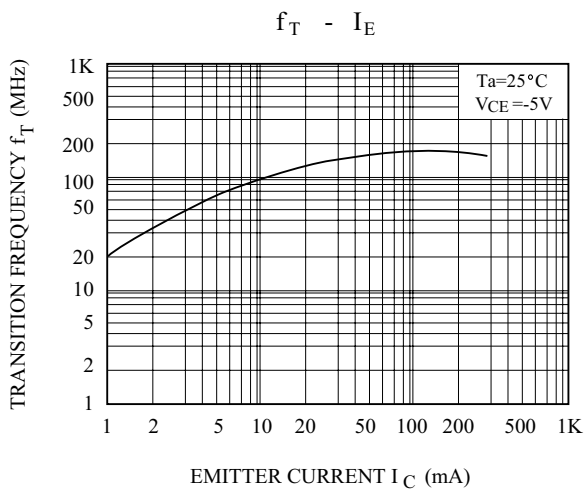
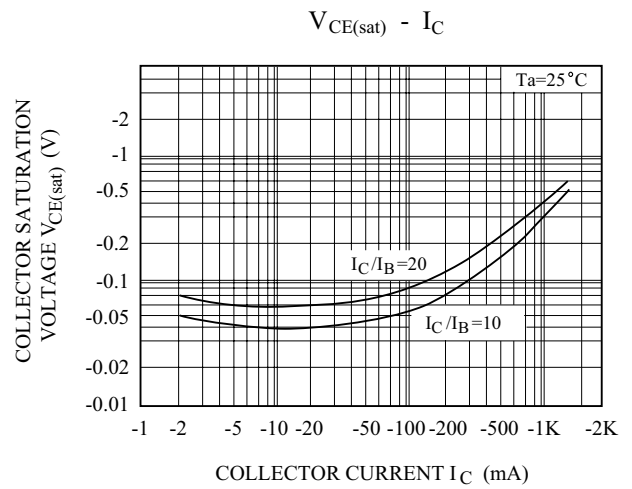
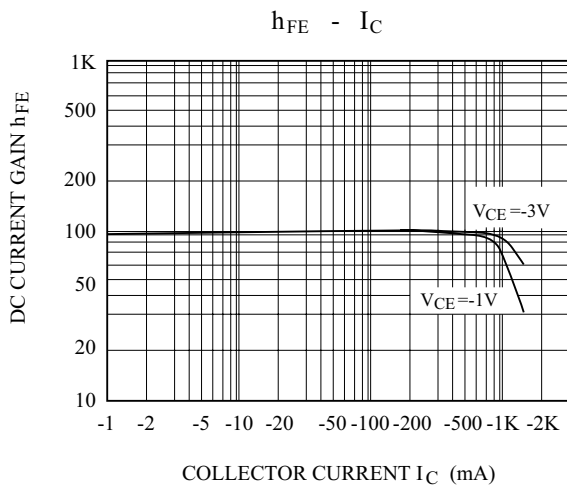
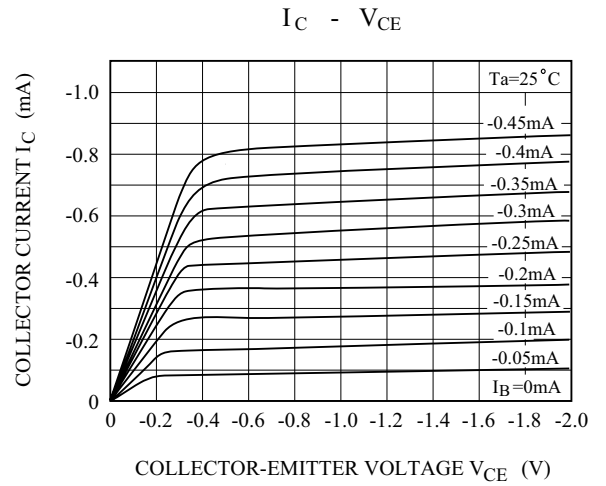
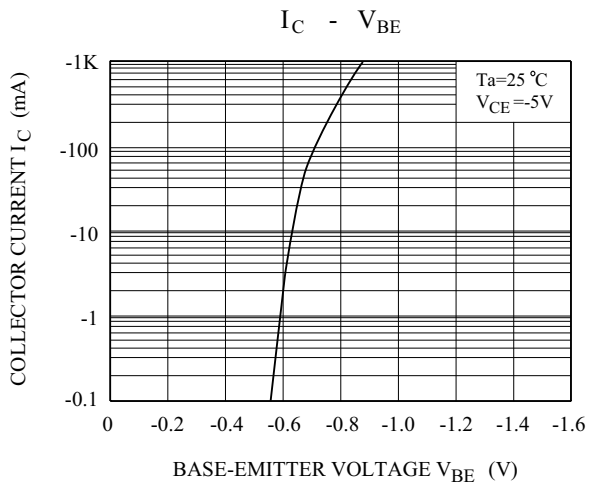


### ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = -60V, I_E = 0$	-	-	-1	μA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = -4V, I_C = 0$	-	-	-1	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-80	-	-	V
DC Current Gain	$h_{FE}(\text{Note})$	$V_{CE} = -3V, I_C = -100mA$	70	-	400	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$	-	-	-0.4	V
Transition Frequency	$f_T$	$V_{CE} = -5V, I_C = -50mA, f = 30MHz$	-	100	-	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$	-	25	-	pF

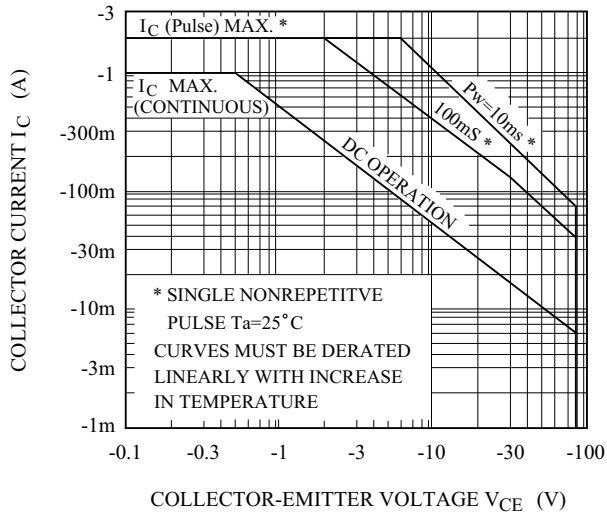
Note : h<sub>FE</sub> Classification    O:70 ~ 140,    Y:120 ~ 240,    GR:200 ~ 400

# KTB1260



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SAFE OPERATING AREA



$P_c - T_a$

